

MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

Monolithic Dual Switching Diodes

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	75	Vdc
D.C. Reverse Voltage MMBD2837LT1G, SMMBD2837LT1G MMBD2838LT1G	V_R	30 50	Vdc
Peak Forward Current	I_{FM}	450 300	mAdc
Average Rectified Current	I_O	150 100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

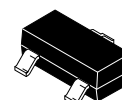
Rating	Symbol	Value	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

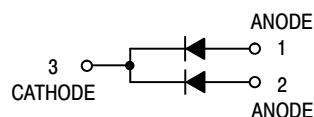


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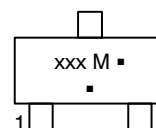
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SOT-23 (TO-236AB)
CASE 318
STYLE 9



MARKING DIAGRAM



xxx = Specific Device Code
A5 = MMBD2837LT1G,
SMMBD2837LT1G
MA6 = MMBD2838LT1G
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBD2837LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD2837LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD2838LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

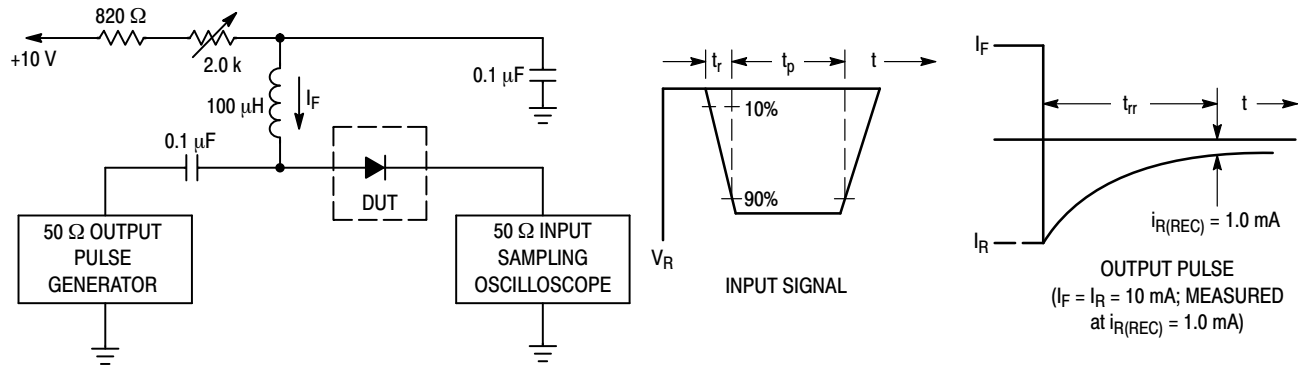
MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

ELECTRICAL CHARACTERISTICS (EACH DIODE) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{BR} = 100 \mu\text{Adc}$) MMBD2837LT1G, SMMBD2837LT1G MMBD2838LT1G	$V_{(BR)}$	35 75	– –	Vdc
Reverse Voltage Leakage Current (Note 3.) ($V_R = 30 \text{ Vdc}$) MMBD2837LT1G, SMMBD2837LT1G ($V_R = 50 \text{ Vdc}$) MMBD2838LT1G	I_R	– –	0.1 0.1	μAdc
Diode Capacitance ($V_R = 0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	–	4.0	pF
Forward Voltage ($I_F = 10 \text{ mAdc}$) ($I_F = 50 \text{ mAdc}$) ($I_F = 100 \text{ mAdc}$)	V_F	– – –	1.0 1.0 1.2	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}$, $I_{R(REC)} = 1.0 \text{ mAdc}$) (Figure 1)	t_{rr}	–	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For each individual diode while the second diode is unbiased.



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.

Notes: 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.

Notes: 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH CATHODE

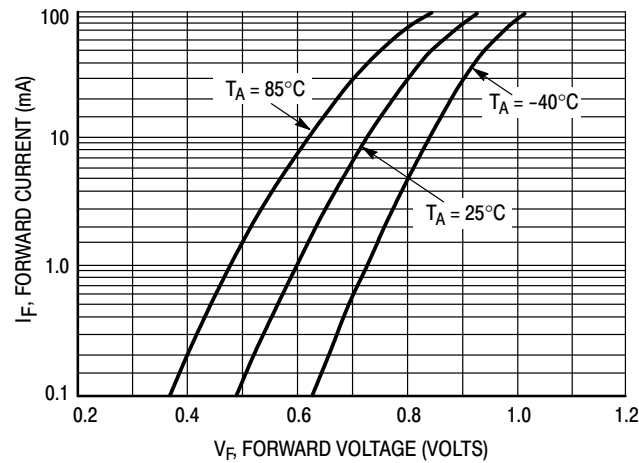


Figure 2. Forward Voltage

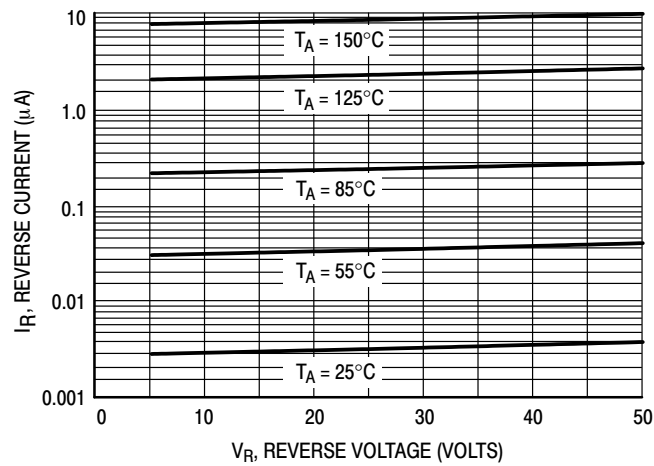


Figure 3. Leakage Current

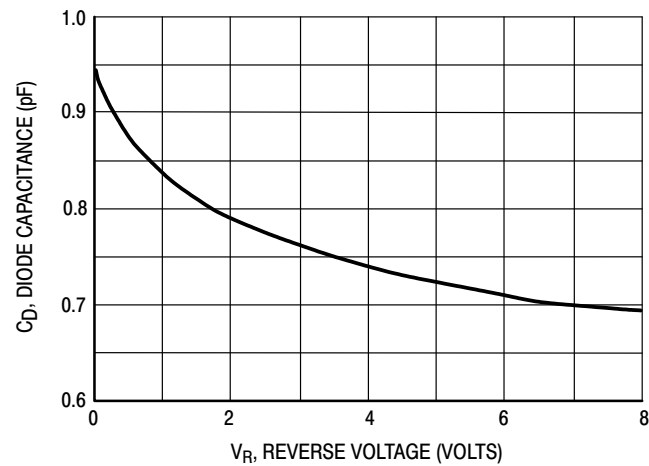


Figure 4. Capacitance

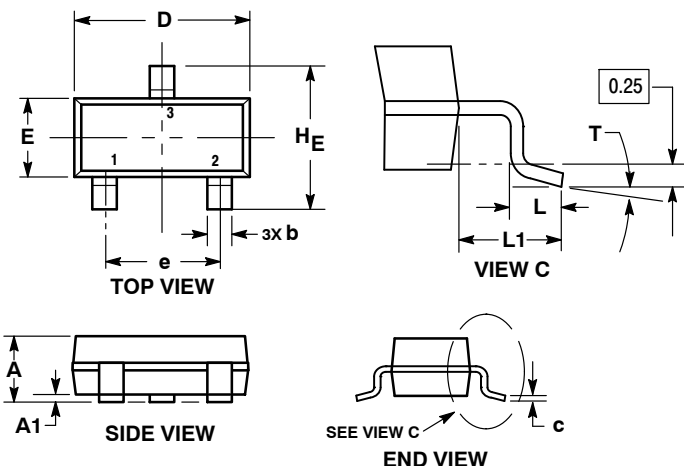
MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08

ISSUE AR



NOTES:

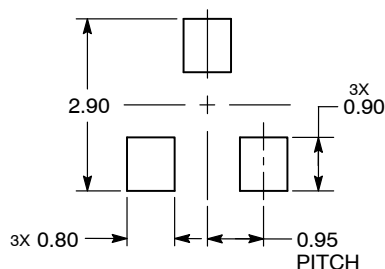
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 9:

- PIN 1. ANODE
- ANODE
- CATHODE

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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